



## DMTH47M2SPSWQ

### 40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I⊳ Max Tc = +25°C
40V	7.5mΩ @ V <sub>GS</sub> = 10V	73A

# Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes Power Losses
- Wettable Flank for Improved Optical Inspection
- Fast Switching Speed
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
  The DMTH47M2SPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- High Frequency Switching
- Synchronous Rectification
- DC-DC Converters

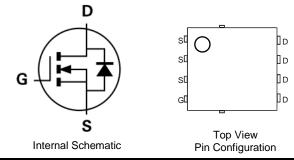


Top View

Bottom View

## **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nulliber	Fackage	Qty.	Carrier	
DMTH47M2SPSWQ-13	PowerDI5060-8 (SWP) (Type UX)	2,500	Tape & Reel	

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

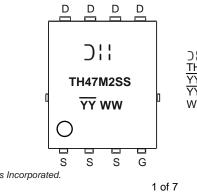
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**

Notes:



);; = Manufacturer's Marking <u>TH47M2SS</u> = Product Type Marking Code <u>YY</u>WW = Date Code Marking <u>YY</u> = Year (ex: 21 = 2021) WW = Week (01 to 53)

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# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		Vdss	40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6), V <sub>GS</sub> = 10V	Tc = +25°C Tc = +100°C	ID	73 51	А
Maximum Continuous Body Diode Forward Current (Note 6)		Is	73	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Ідм	292	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Isм	292	A
Avalanche Current, L = 0.1mH		las	24.7	A
Avalanche Energy, L = 0.1mH		Eas	30.5	mJ

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	3.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	45	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	68	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	2.2	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	T.m	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol	IVIIII	Тур	wax	Unit	Test Condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40			V	Vgs = 0V, Id = 250µA	
Zero Gate Voltage Drain Current				1	μÂ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	1000		1	2.00		100 - 1201, 100 - 01	
Gate Threshold Voltage	VGS(TH)	2		4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	_	5.8	7.5	mΩ	VGS = 10V, ID = 20A	
Diode Forward Voltage	V <sub>SD</sub>		0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)						-	
Input Capacitance	Ciss	_	897	_		V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss		530		pF		
Reverse Transfer Capacitance	Crss	_	12.4	_			
Gate Resistance	Rg		2.07		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	12.1	-			
Gate-Source Charge	Q <sub>gs</sub>		2.0		nC	$V_{DD} = 20V, I_D = 20A, V_{GS} = 10V$	
Gate-Drain Charge	Q <sub>gd</sub>		1.9				
Turn-On Delay Time	td(on)		5.4				
Turn-On Rise Time	t <sub>R</sub>		4.5		ns	$\label{eq:VDD} \begin{split} V_{DD} &= 20V, \ V_{GS} = 10V, \\ R_g &= 3\Omega, \ I_D = 20A \end{split}$	
Turn-Off Delay Time	tD(OFF)		12.1		115		
Turn-Off Fall Time	t⊨		5.6	-			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	39.1	_	ns		
Body Diode Reverse Recovery Charge	Qrr		53.3		nC	- I <sub>F</sub> = 20A, di/dt = 100A/μs	

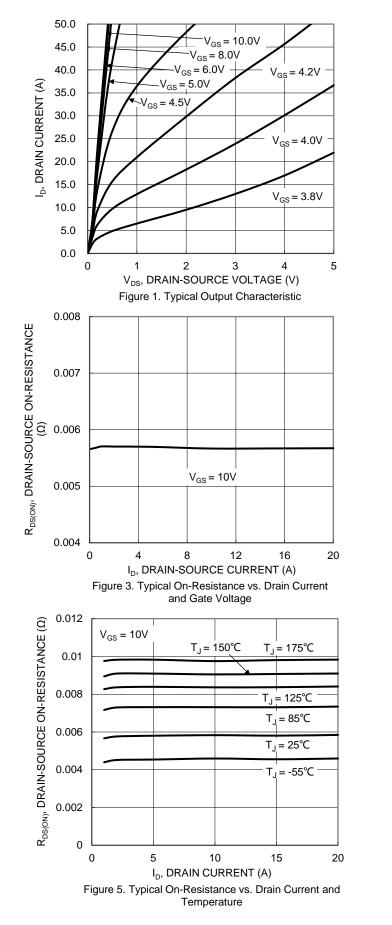
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. Notes:

Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



## DMTH47M2SPSWQ



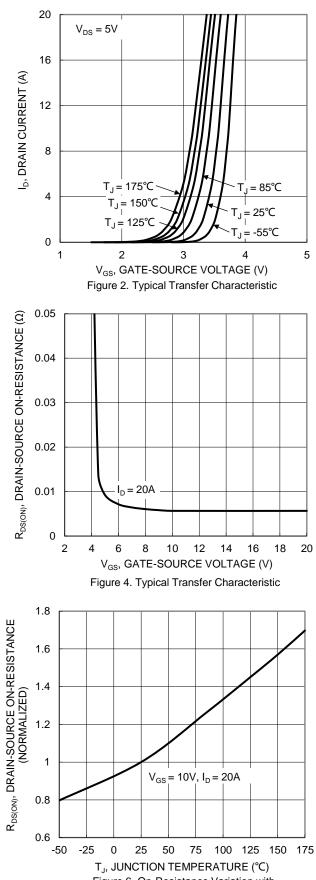


Figure 6. On-Resistance Variation with Junction Temperature



# DMTH47M2SPSWQ

 $I_D = 1mA$ 

100 125 150 175

Ciss

Cos

 $C_{rss}$ 

35

40

75

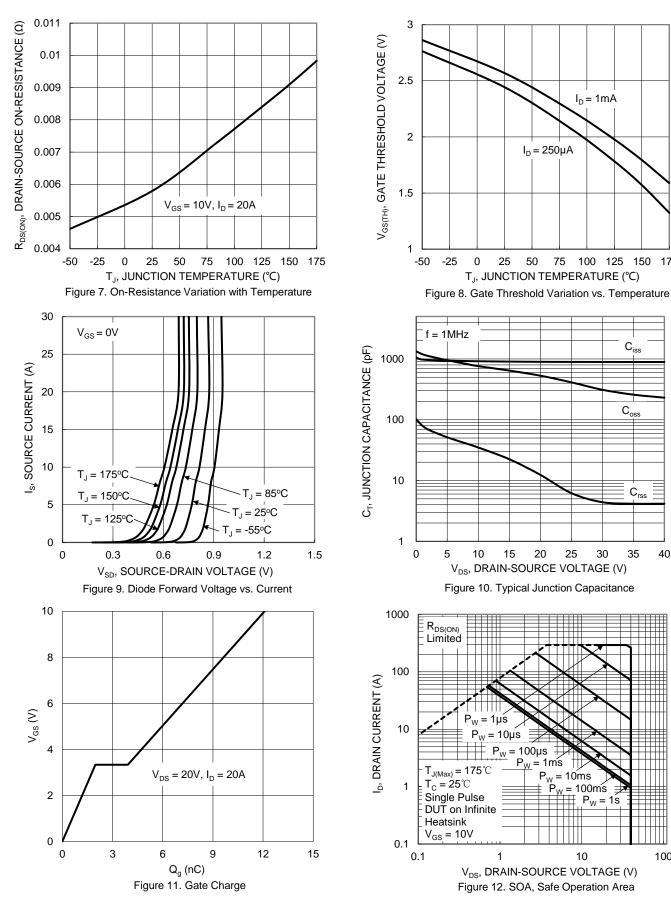
25

30

 $P_W =$ 

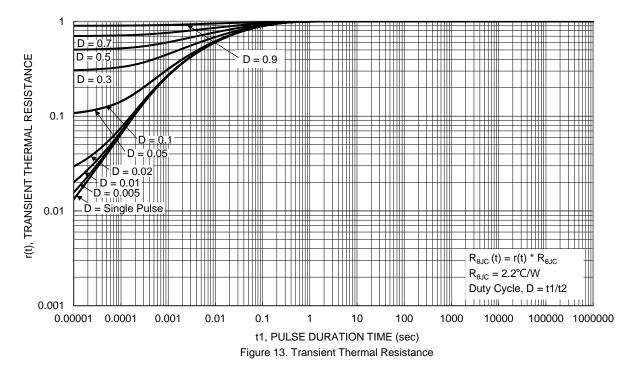
10

1s



100



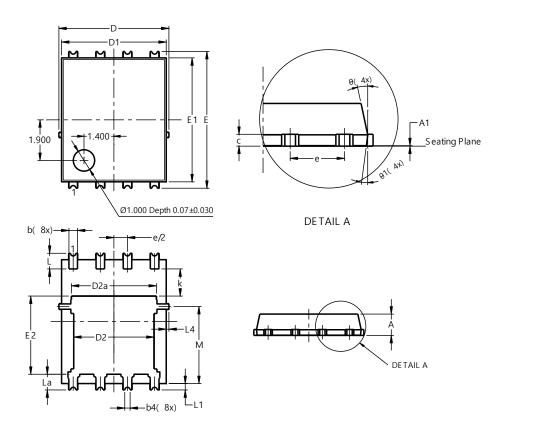




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)

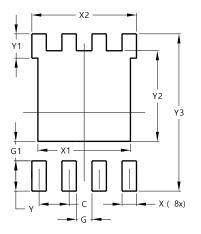


Pov	PowerDI5060-8 (SWP) (Type UX)				
Dim			Тур		
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	0	).25REF	-		
С	0.230	0.330	0.277		
D	5	.15 BS0	2		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
E	6	.40 BS0	2		
E1	5.60	5.60 6.00			
E2	3.46	3.86	3.66		
E2a			4.395		
е		.27BSC	;		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All	Dimensi	ons in	mm		

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)



Value (in mm)			
1.270			
0.660			
0.820			
0.610			
4.100			
4.420			
1.270			
1.020			
3.810			
6.610			



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